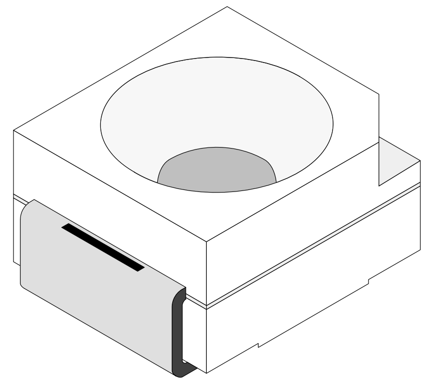
GaAs Infrared Emitting Diode in SMT Package

Description

TSMS3700 is a standard GaAs infrared emitting diode in a miniature PL–CC–2 package.
Its flat window provides a wide aperture, making it ideal for use with external optics.
The diode is case compatible to the TEMT3700 phototransistor, allowing the user to assemble his own optical interrupters.



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Features

- SMT IRED with high radiant power
- Low forward voltage
- Compatible with automatic placement equipment
- EIA and ICE standard package
- Suitable for infrared, vapor phase and wave-solder process
- Available in 8 mm tape
- Suitable for DC or high pulse current operation
- Extra wide angle of half intensity $\varphi = \pm 60^\circ$
- Peak wavelength λ_p = 950 nm
- High reliability
- Matching to TEMT3700 phototransistor

Applications

Infrared source in tactile keyboards
IR diode in low space applications
Matching with phototransistor TEMT3700 in reflective sensors
PCB mounted infrared sensors
Infrared emitter for miniature light barriers

Absolute Maximum Ratings

T_{amb} = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		V_R	5	V
Forward Current		I_F	100	mA
Peak Forward Current	t_p/T=0.5, t_p=100 µs	I_{FM}	200	mA
Surge Forward Current	t_p=100 µs	I_{FSM}	1.5	A
Power Dissipation		P_V	170	mW
Junction Temperature		T_j	100	°C
Operating Temperature Range		T_{amb}	–55...+100	°C
Storage Temperature Range		T_{stg}	–55...+100	°C
Soldering Temperature	t ≦ 10sec	T_{sd}	260	°C
Thermal Resistance Junction/Ambient	on PC board	R_{thJA}	450	K/W

Basic Characteristics

T_{amb} = 25°C

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.3	1.7	V
Forward Voltage	I_F = 1 A, t_p = 100 µs	V_F		1.8		V
Temp. Coefficient of V_F	I_F = 100mA	TK_{VF}		–1.3		mV/K
Reverse Current	V_R = 5 V	I_R			100	µA
Junction Capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		30		pF
Radiant Intensity	I_F = 100 mA, t_p = 20 ms	I_e	1.6	4.5		mW/sr
	I_F = 1.5 A, t_p = 100 µs	I_e		35		mW/sr
Radiant Power	I_F = 100 mA, t_p = 20 ms	ϕ_e		12		mW
Temp. Coefficient of ϕ_e	I_F = 100 mA	$TK_{\phi e}$		–0.8		%/K
Angle of Half Intensity		φ		±60		deg
Peak Wavelength	I_F = 100 mA	λ_p		950		nm
Spectral Bandwidth	I_F = 100 mA	$\Delta\lambda$		50		nm
Temp. Coefficient of λ_p	I_F = 100 mA	$TK_{\lambda p}$		0.2		nm/K
Rise Time	I_F = 20 mA	t_r		800		ns
	I_F = 1 A	t_r		400		ns
Fall Time	I_F = 20 mA	t_f		800		ns
	I_F = 1 A	t_f		400		ns

Typical Characteristics (T_{amb} = 25°C unless otherwise specified)

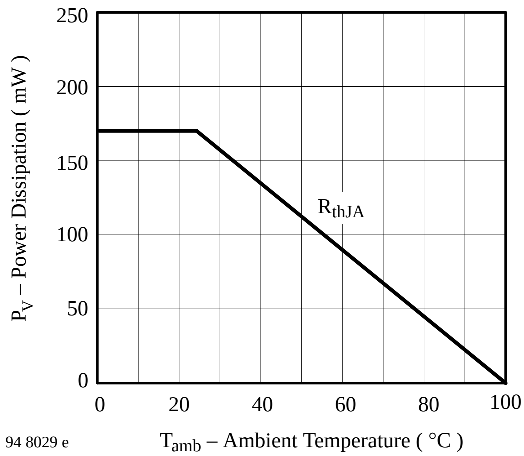


Figure 1 : Power Dissipation vs. Ambient Temperature

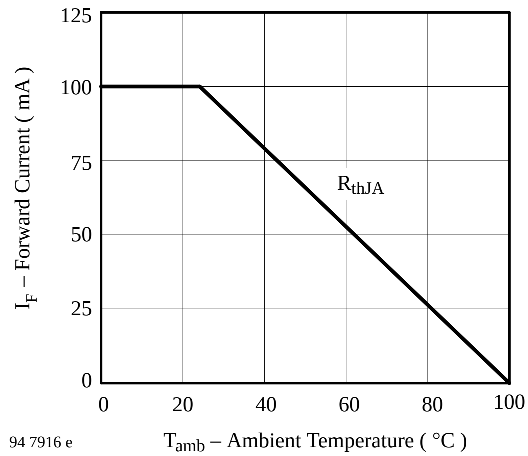
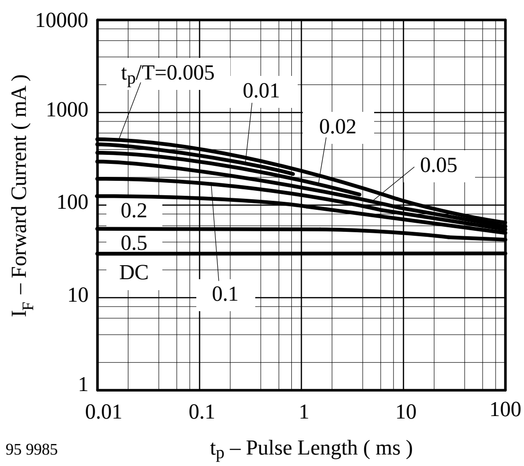


Figure 2 : Forward Current vs. Ambient Temperature



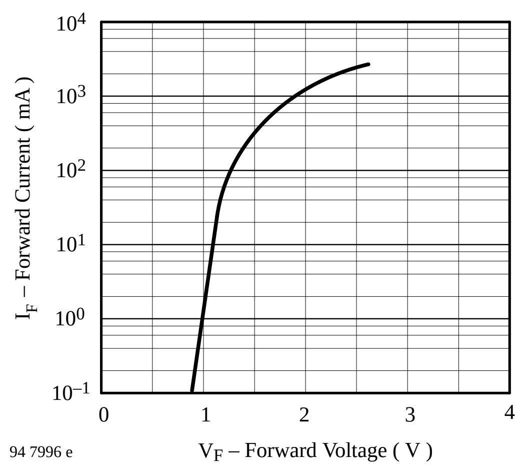


Figure 4 : Forward Current vs. Forward Voltage

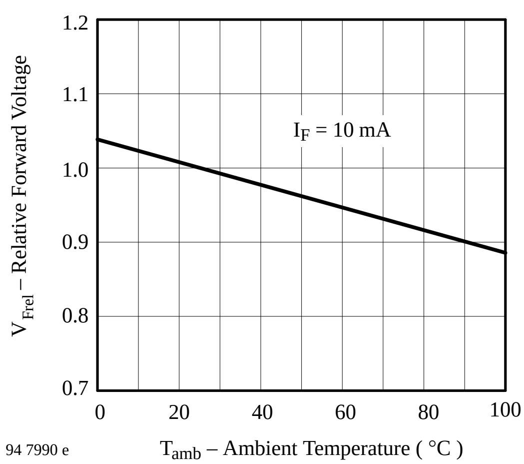


Figure 5 : Relative Forward Voltage vs. Ambient Temperature

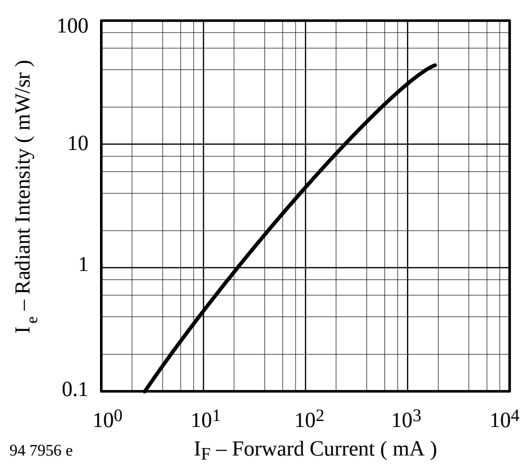


Figure 6 : Radiant Intensity vs. Forward Current

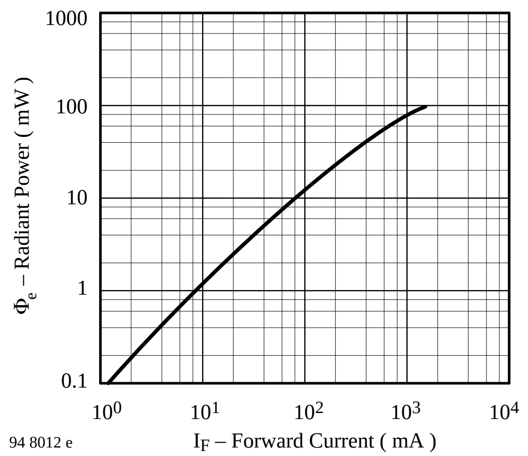


Figure 7 : Radiant Power vs. Forward Current

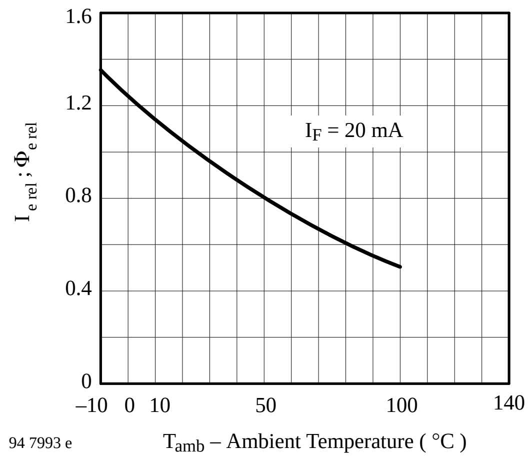


Figure 8 : Rel. Radiant Intensity\Power vs. Ambient Temperature

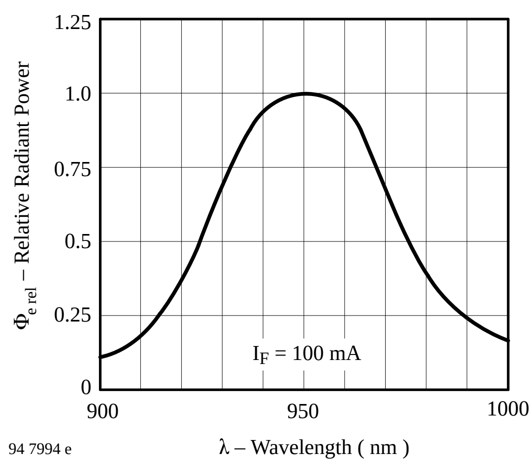


Figure 9 : Relative Radiant Power vs. Wavelength

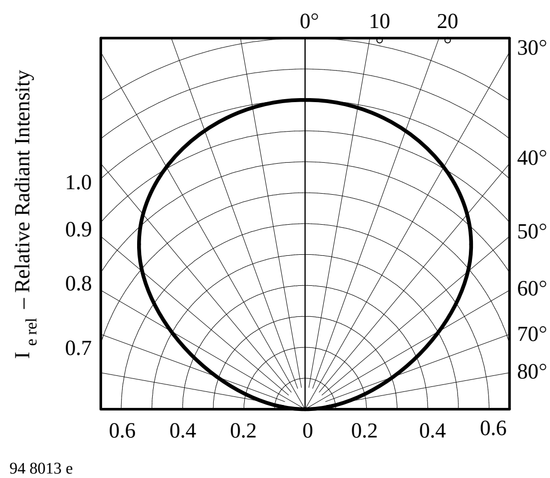
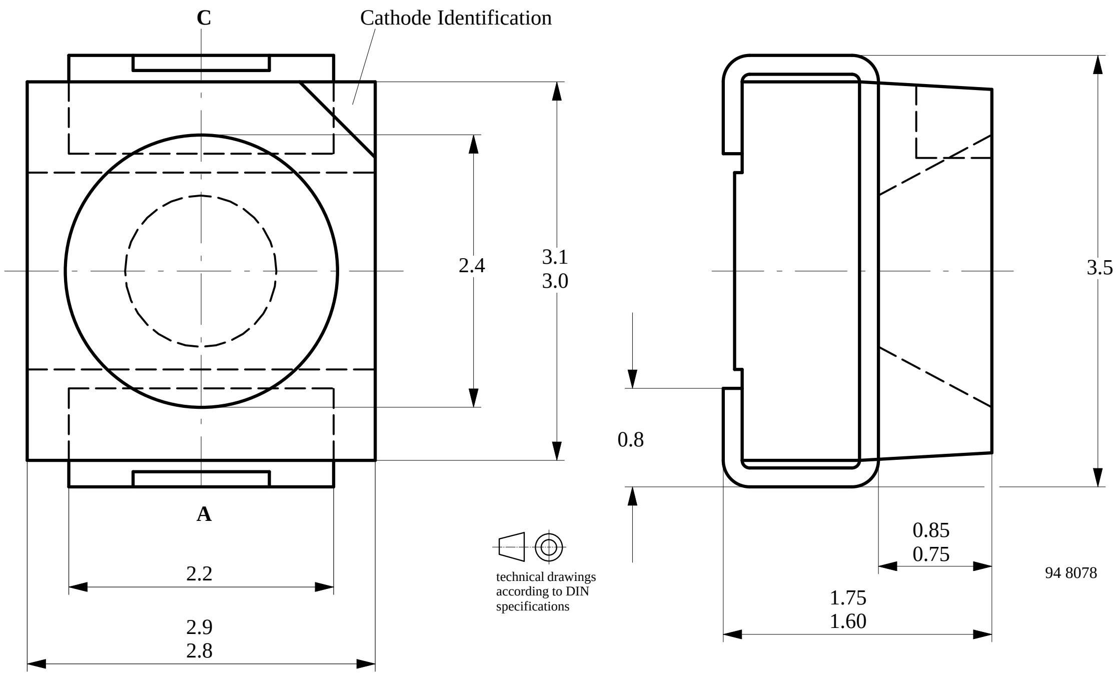


Figure 10 : Relative Radiant Intensity vs. Angular Displacement

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively

2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA

3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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